

General Description

The WSP05N15 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP05N15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

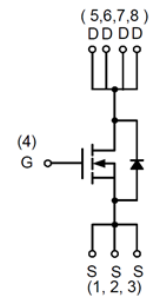
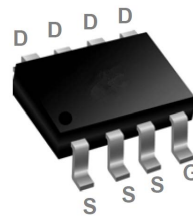
Product Summary

BVDSS	RDSON	ID
150V	37mΩ	6A

Applications

- Power Management for Boost Converters.
- Synchronous Rectifiers for SMPS.
- LED Backlighting.

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 25	V
$I_D @ T_c = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.0	A
$I_D @ T_c = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.8	A
I_{DM}	Pulsed Drain Current ²	24	A
EAS	Single Pulse Avalanche Energy ³	36	mJ
I_{AS}	Avalanche Current	12	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ⁴	3.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	70	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	24	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	150	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =6A	---	37	45	mΩ
		V _{GS} =6V, I _D =2A	---	48	78	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.52	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	10	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	6.2	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	3.2	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =3A	---	23	33	nC
Q _{gs}	Gate-Source Charge		---	6	---	
Q _{gd}	Gate-Drain Charge		---	9.9	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =6Ω I _D =1A, R _L =30Ω.	---	5.5	21.6	ns
T _r	Rise Time		---	27	48.6	
T _{d(off)}	Turn-Off Delay Time		---	56	112	
T _f	Fall Time		---	24	48	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	1760	---	pF
C _{oss}	Output Capacitance		---	90	---	
C _{rss}	Reverse Transfer Capacitance		---	45	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.5mH, I _{AS} =12A	30	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	4.0	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	24	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =4A, T _J =25°C	---	---	1.3	V
t _{rr}	Reverse Recovery Time	IF=6A, dI/dt=100A/μs, T _J =25°C	---	31	---	nS
Q _{rr}	Reverse Recovery Charge		---	50	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper,t<10sec.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=12A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

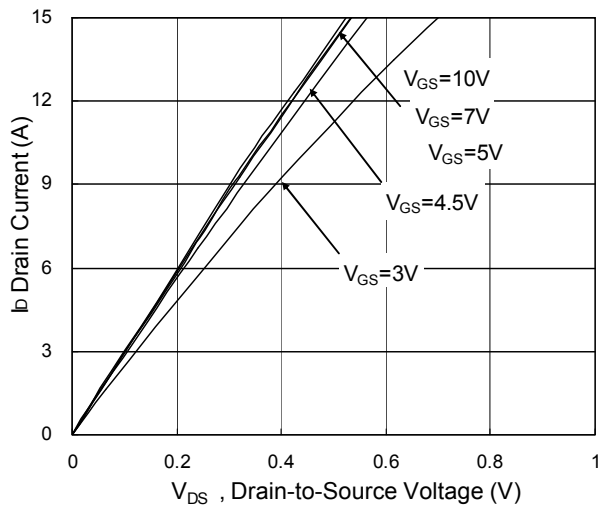


Fig.1 Typical Output Characteristics

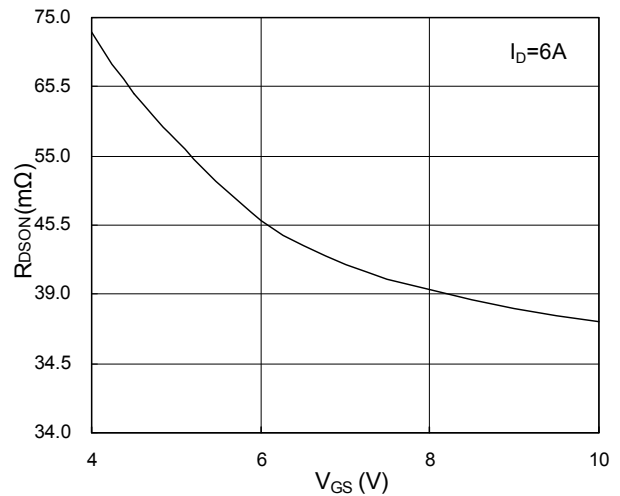


Fig.2 On-Resistance vs. Gate-Source

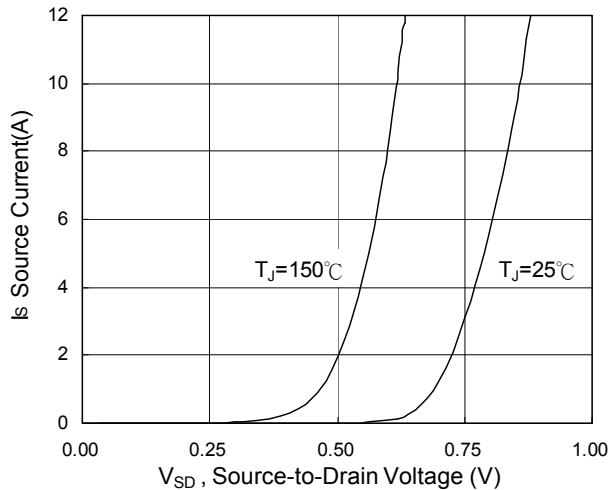


Fig.3 Forward Characteristics Of Reverse

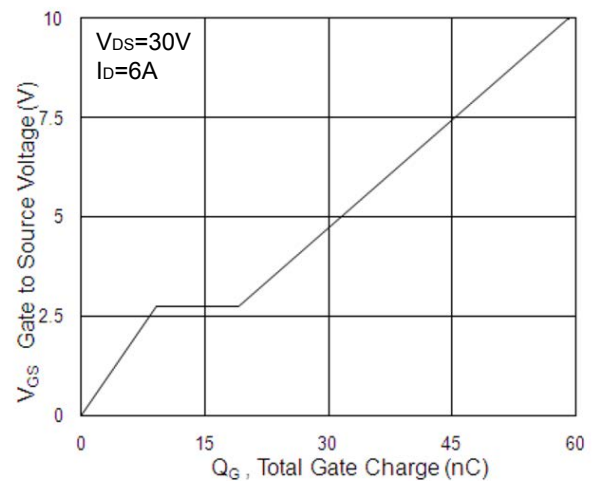


Fig.4 Gate-Charge Characteristics

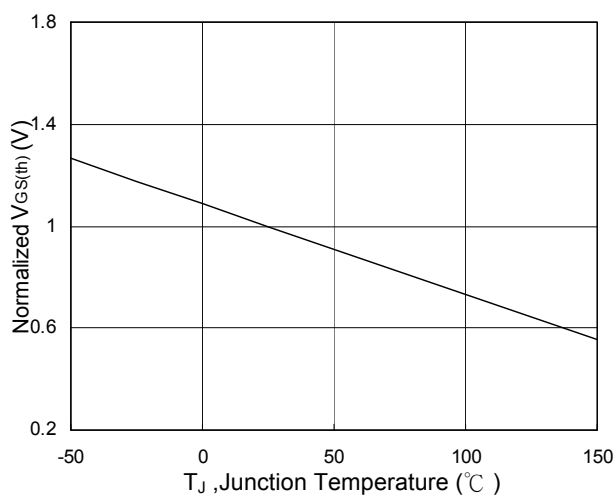


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

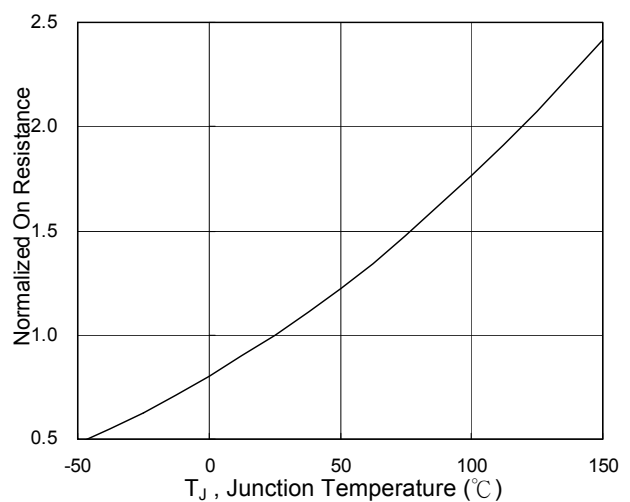


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

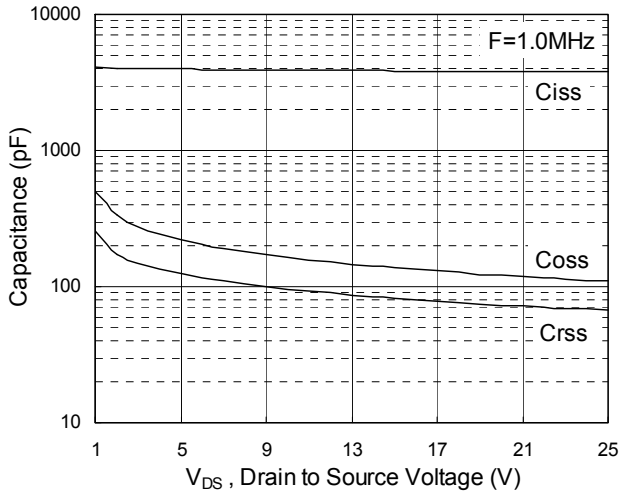


Fig.7 Capacitance

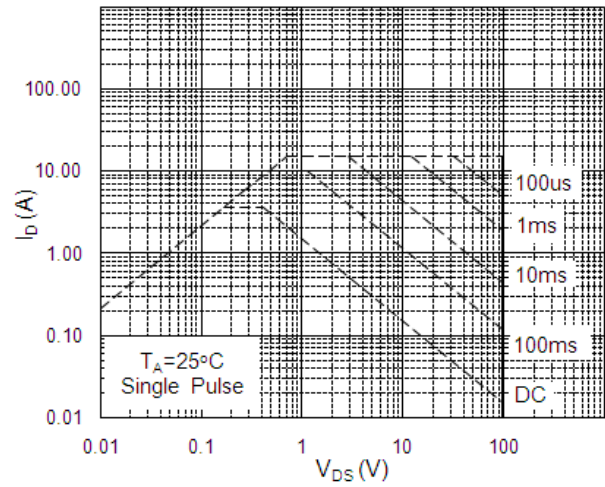


Fig.8 Safe Operating Area

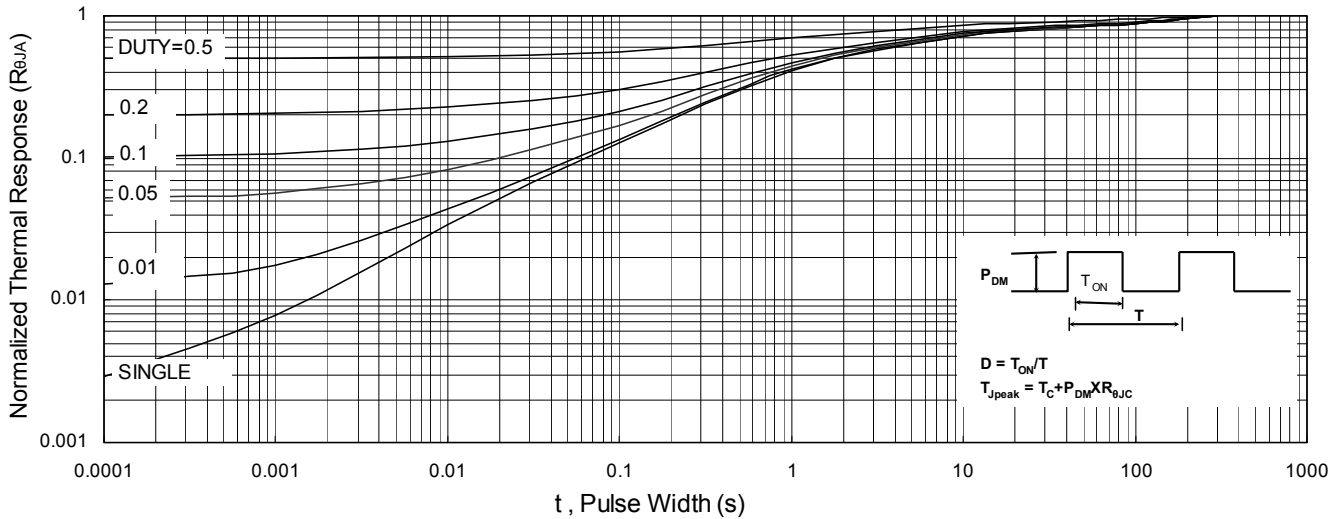


Fig.9 Normalized Maximum Transient Thermal Impedance

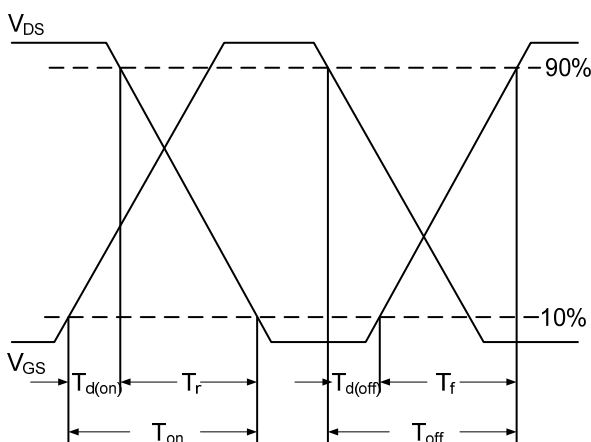


Fig.10 Switching Time Waveform

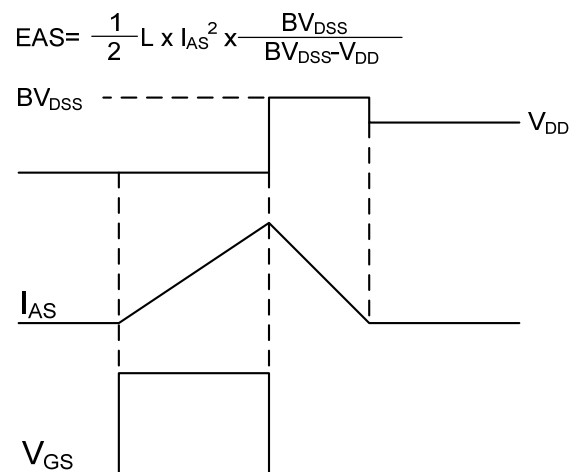


Fig.11 Unclamped Inductive Switching Waveform

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